



BC846BLP4

65V NPN SMALL SIGNAL SURFACE MOUNT TRANSISTOR

Features

- Low Collector-Emitter Saturation Voltage, VCE(SAT)
- Ultra-Small Leadless Surface Mount Package
- Totally Lead-Free & Fully RoHS Compliant (Note 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: X2-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu, Solderable per MIL-STD-202, Method 208 @4
- Weight: 0.0009 grams (Approximate)

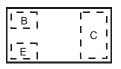
X2-DFN1006-3



Bottom View



Device Symbol



Top View Device Schematic

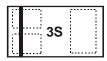
Ordering Information (Note 4)

Part Number	Marking	Reel Size (in)	Tape Width (mm)	Quantity per Reel
BC846BLP4-7B	3S	7	8	10,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



Top View Bar Denotes Base and Emitter Side

3S = Product Type Marking Code



Maximum Ratings $(@T_A = +25^{\circ}C, \text{ unless otherwise specified.})$

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	80	V
Collector-Emitter Voltage	V _{CEO}	65	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current - Continuous	I _C	100	mA
Peak Collector Current	I _{CM}	200	mA
Peak Emitter Current	I _{EM}	200	mA

Thermal Characteristics

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 5)		0.46	W	
Power Dissipation	(Note 6)	P _D	1		
Thermal Resistance, Junction to Ambient	(Note 5)	Ъ	272	°C/W	
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{ hetaJA}$	120	C/VV	
Thermal Resistance, Junction to Leads (Note 7)		$R_{ heta JL}$	110	°C/W	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C	

ESD Ratings (Note 8)

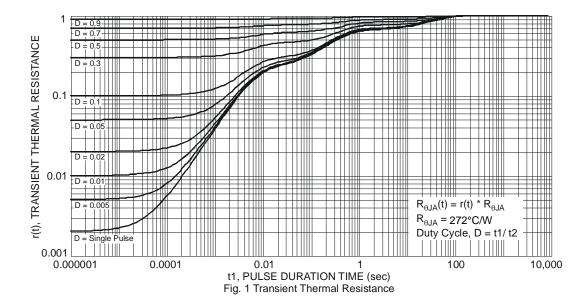
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	200	V	В

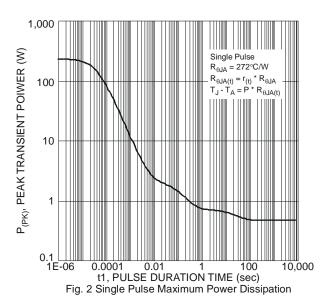
Notes:

- 5. For a device surface mounted on minimum recommended pad layout FR-4 PCB with single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition. The entire exposed collector pad is attached to the heatsink.
- 6. Same as Note 5, except device is surface mounted on 25mm X 25mm collector pad heatsink with 1oz copper.
- 7. Thermal resistance from junction to solder-point (at the end of the collector lead).
- 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics





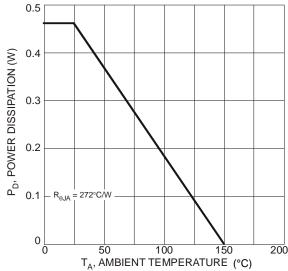


Fig. 3 Power Dissipation vs. Ambient Temperature



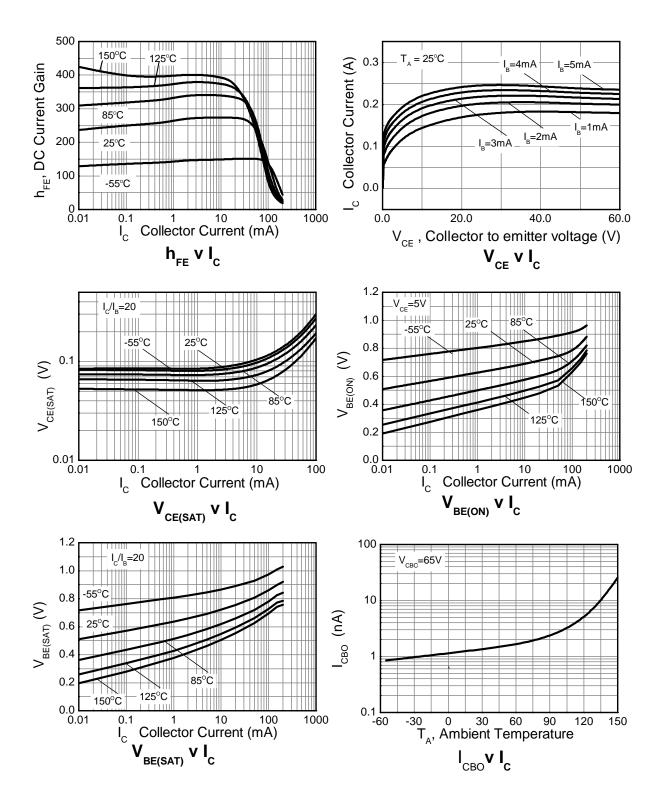
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Collector-Base Breakdown Voltage	BV _{CBO}	80			V	$I_C = 100\mu A, I_E = 0$	
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CEO}	65	_	_	V	$I_C = 10 \text{mA}, I_B = 0$	
Emitter-Base Breakdown Voltage	BV _{EBO}	6	_	_	V	$I_E = 100 \mu A, I_C = 0$	
Collector Cutoff Current	I _{CES}	_	_	15	nA	V _{CE} = 65V	
Collector Cutoff Current	1		_	15	nA	$V_{CB} = 40V$	
	I _{CBO}			5.0	μΑ	$V_{CB} = 30V, T_A = +150^{\circ}C$	
ON CHARACTERISTICS (Note 9)							
DC Current Gain	h _{FE}	200	270	450	_	$V_{CE} = 5V$, $I_C = 2.0mA$	
Collector-Emitter Saturation Voltage	Vorces		90	250	mV	$I_C = 10mA, I_B = 0.5mA$	
Concetor Emitter Cataration Voltage	V _{CE(SAT)}		220	600	111 V	$I_C = 100 \text{mA}, I_B = 5.0 \text{mA}$	
Base-Emitter Saturation Voltage	Various	_	720	900	mV	$I_C = 10 \text{mA}, I_B = 0.5 \text{mA}$	
Dase-Emilier Saturation Voltage	V _{BE(SAT)}		870	_	111 V	$I_C = 100 \text{mA}, I_B = 5.0 \text{mA}$	
Base-Emitter Voltage	Vaccoun	580	650	700 770	mV	$V_{CE} = 5V$, $I_C = 2.0mA$	
	V _{BE(ON)}	_	—			$V_{CE} = 5V$, $I_C = 10mA$	
SMALL SIGNAL CHARACTERISTICS (Note 9)	SMALL SIGNAL CHARACTERISTICS (Note 9)						
Input Capacitance	C _{ibo}		6.7		pF	$V_{CB} = 5V$, $f = 1.0MHz$	
Output Capacitance	C_{obo}		1.76		рF	$V_{CB} = 10V, f = 1.0MHz$	
Current Gain-Bandwidth Product	f⊤	100	300		MHz	$V_{CE} = 5V, I_{C} = 10mA, f = 100MHz$	
Noise Figure	NF	_	2	10	dB	$V_{CE} = 5V$, $I_{C} = 200\mu A$, $R_{S} = 2.0k\Omega$, $f = 1.0kHz$, $\Delta f = 200Hz$	
Delay Time	t _D		11.2	_	ns	.,	
Rise Time	t _R	_	59.7	_	ns	$V_{CC} = 30V$,	
Storage Time	ts	_	190.8	_	ns	$I_C = 150 \text{mA},$ $I_{B1} = -I_{B2} = 15 \text{mA}$	
Fall Time	t _F		108.6		ns	181 - 182 = 13111A	

Note: 9. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.

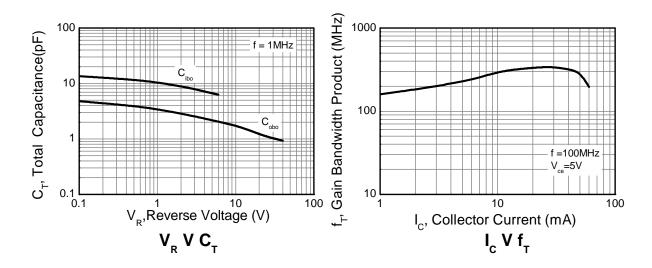


Typical Electrical Characteristics





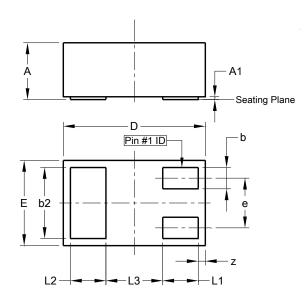
Typical Electrical Characteristics (Cont.)



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

X2-DFN1006-3



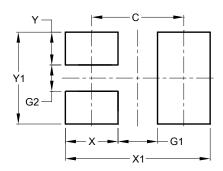
X2-DFN1006-3					
Dim	Min	Max	Тур		
Α	_	0.40	_		
A1	0.00	0.05	0.03		
b	0.10	0.20	0.15		
b2	0.45	0.55	0.50		
D	0.95	1.05	1.00		
E	0.55	0.65	0.60		
е	1	1	0.35		
L1	0.20	0.30	0.25		
L2	0.20	0.30	0.25		
L3	-	-	0.40		
Z	0.02	0.08	0.05		
All Dimensions in mm					



Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

X2-DFN1006-3



Dimensions	Value (in mm)
С	0.70
G1	0.30
G2	0.20
Х	0.40
X1	1.10
Y	0.25
Y1	0.70

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